

N-Channel Enhancement Mode Power MOSFET

MTN4410V8

| | |
|--|------------|
| BV _{DSS} | 30V |
| I _D @V _{GS} =10V, T _A =25°C | 12A |
| I _D @V _{GS} =10V, T _C =25°C | 30A |
| R _{DS(on)} @V _{GS} =10V, I _D =10A | 9 mΩ (typ) |
| R _{DS(on)} @V _{GS} =4.5V, I _D =6A | 14mΩ (typ) |

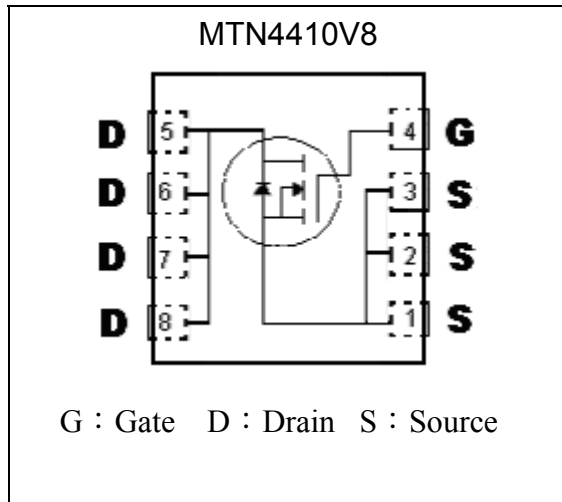
Features

- Single Drive Requirement
- Low On-resistance
- Pb-free lead plating package

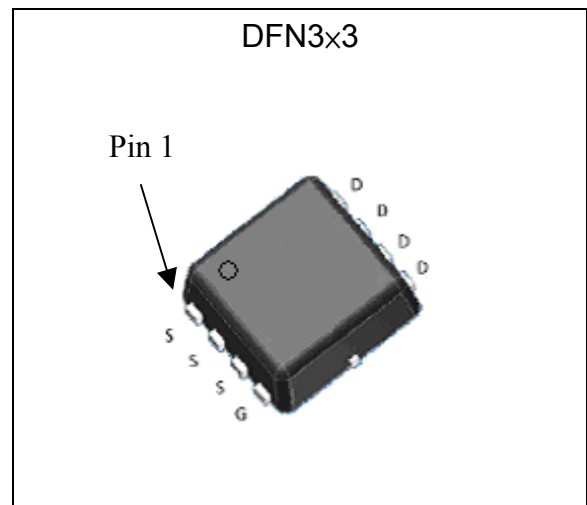
Applications

- Synchronous rectifier for DC/DC converters
- Telecom secondary side rectification
- High end server/ work station

Symbol

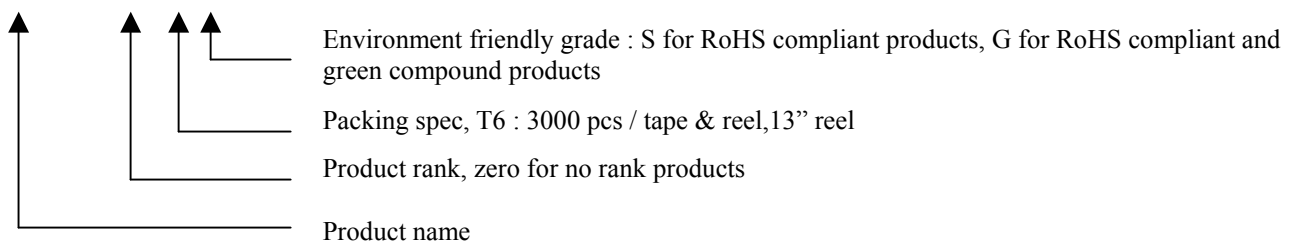


Outline



Ordering Information

| Device | Package | Shipping |
|------------------|---|------------------------|
| MTN4410V8-0-T6-G | DFN3x3 (Pb-free lead plating and halogen-free package) | 3000 pcs / Tape & Reel |





Absolute Maximum Ratings (Ta=25°C)

| Parameter | Symbol | Limits | Unit |
|---|-----------------------------------|----------|------|
| Drain-Source Voltage | V _{DS} | 30 | V |
| Gate-Source Voltage | V _{GS} | ±20 | |
| Continuous Drain Current @V _{GS} =10V, T _A =25°C | I _D | 12 | A |
| Continuous Drain Current @V _{GS} =10V, T _A =70°C | | 9.6 | |
| Continuous Drain Current @V _{GS} =10V, T _C =25°C | | 30 | |
| Continuous Drain Current @V _{GS} =10V, T _C =100°C | | 19 | |
| Pulsed Drain Current | I _{DM} | 50 *1 | |
| Total Power Dissipation @ T _A =25°C | P _D | 2.5 | W |
| Linear Derating Factor | | 0.02 | W/°C |
| Operating Junction and Storage Temperature | T _j , T _{stg} | -55~+150 | °C |

Thermal Data

| Parameter | Symbol | Value | Unit |
|--|------------------|-------|------|
| Thermal Resistance, Junction-to-case, max | R _{θJC} | 8 | °C/W |
| Thermal Resistance, Junction-to-ambient, max | R _{θJA} | 50 *3 | |

Note : 1. Pulse width limited by maximum junction temperature
 2. Surface mounted on 1 in² copper pad of FR-4 board, t≤10s ; 125°C/W when mounted on minimum copper pad.

Characteristics (Tj=25°C, unless otherwise specified)

| Symbol | Min. | Typ. | Max. | Unit | Test Conditions |
|-------------------------------------|------|------|------|------|---|
| Static | | | | | |
| BV _{DSS} | 30 | - | - | V | V _{GS} =0V, I _D =250μA |
| ΔBV _{DSS} /ΔT _j | - | 0.02 | - | V/°C | Reference to 25°C, I _D =1mA |
| V _{GS(th)} | 1.0 | 1.6 | 3.0 | V | V _{DS} = V _{GS} , I _D =250μA |
| G _{FS} | - | 20 | - | S | V _{DS} =10V, I _D =10A |
| I _{GSS} | - | - | ±100 | nA | V _{GS} =±20V |
| I _{DSS} | - | - | 1 | μA | V _{DS} =30V, V _{GS} =0V |
| I _{DSS} | - | - | 25 | | V _{DS} =24V, V _{GS} =0V, T _j =55°C |
| *R _{DS(ON)} | - | 9 | 13.5 | mΩ | V _{GS} =10V, I _D =10A |
| *R _{DS(ON)} | - | 14 | 20 | | V _{GS} =4.5V, I _D =6A |
| Dynamic | | | | | |
| *Q _g | - | 16 | - | nC | I _D =10A, V _{DS} =15V, V _{GS} =5V |
| *Q _{gs} | - | 3.8 | - | | |
| *Q _{gd} | - | 6.2 | - | | |
| *t _{d(ON)} | - | 7.5 | - | ns | V _{DS} =25V, I _D =1A, V _{GS} =5V, R _G =3.3Ω, R _D =25Ω |
| *t _r | - | 17 | - | | |
| *t _{d(OFF)} | - | 36 | - | | |
| *t _f | - | 15 | - | | |



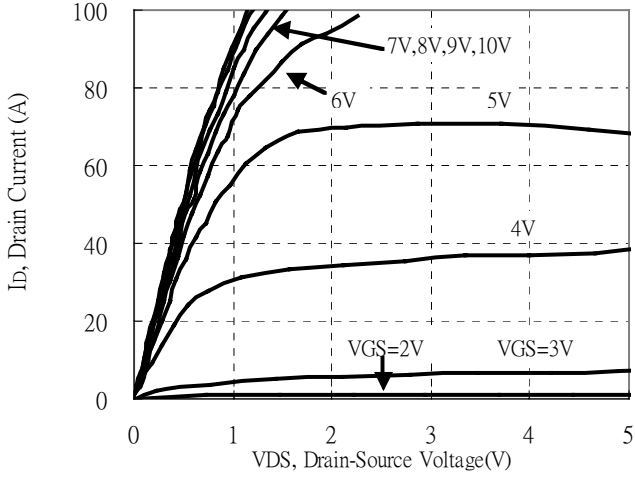
| | | | | | |
|---------------------------|---|------|-----|----|--|
| Ciss | - | 1119 | - | pF | V _{GS} =0V, V _{DS} =15V, f=1MHz |
| Coss | - | 124 | - | | |
| Crss | - | 105 | - | | |
| Source-Drain Diode | | | | | |
| *V _{SD} | - | - | 1.3 | V | I _S =2.3A, V _{GS} =0V |
| *I _S | - | - | 2.3 | A | V _D =V _G =0V, V _S =1.3V |
| *I _{SM} | - | - | 50 | | |

*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

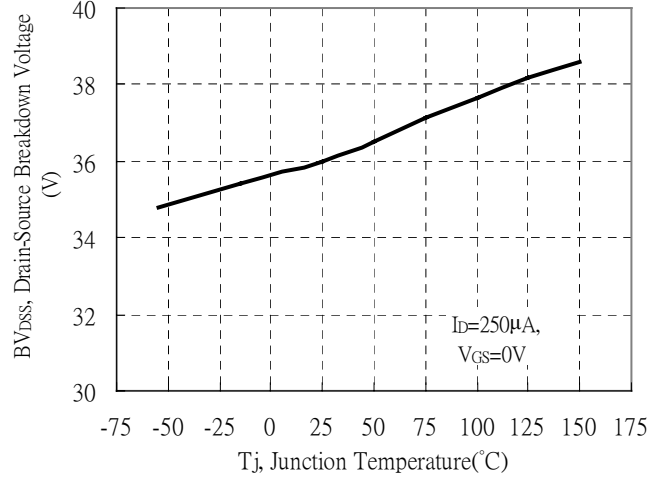


Typical Characteristics

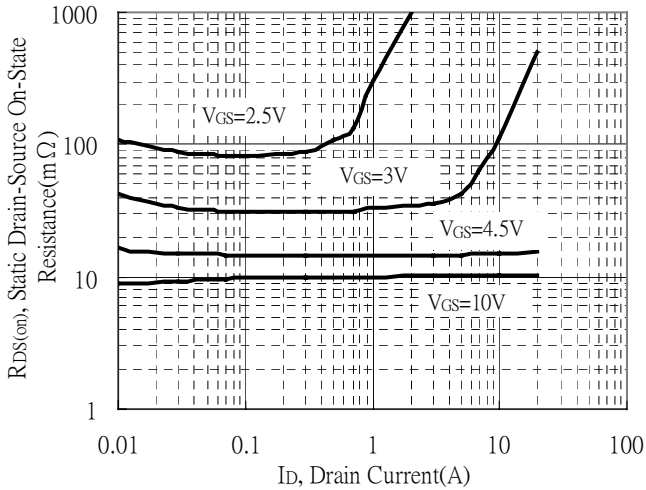
Typical Output Characteristics



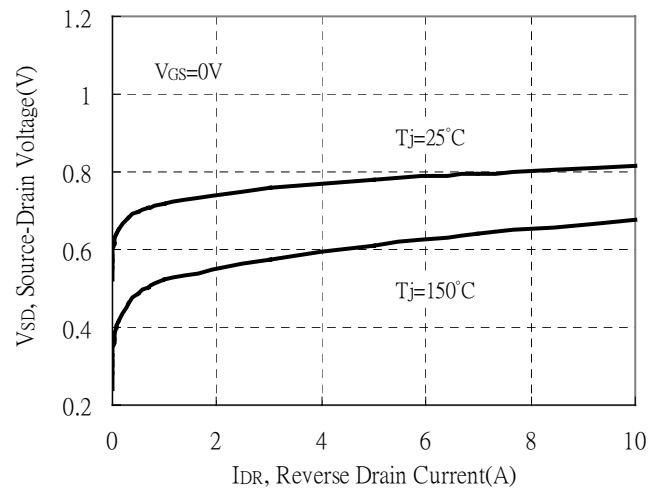
Brekdown Voltage vs Ambient Temperature



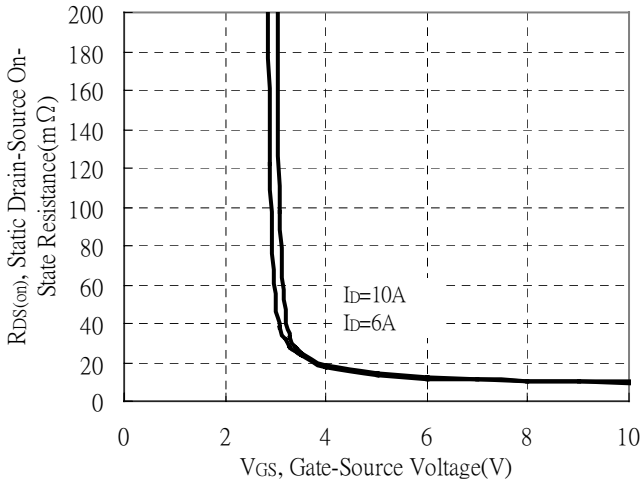
Static Drain-Source On-State resistance vs Drain Current



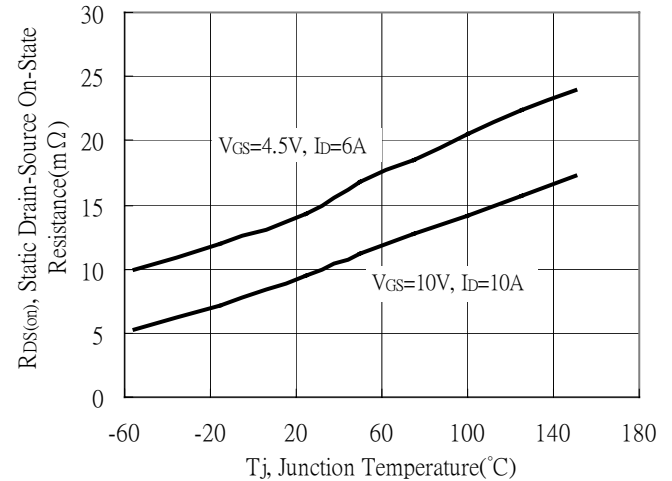
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage



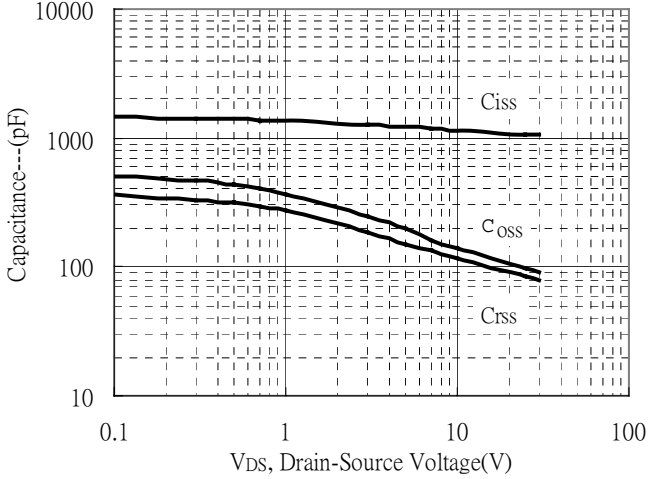
Drain-Source On-State Resistance vs Junction Temperature



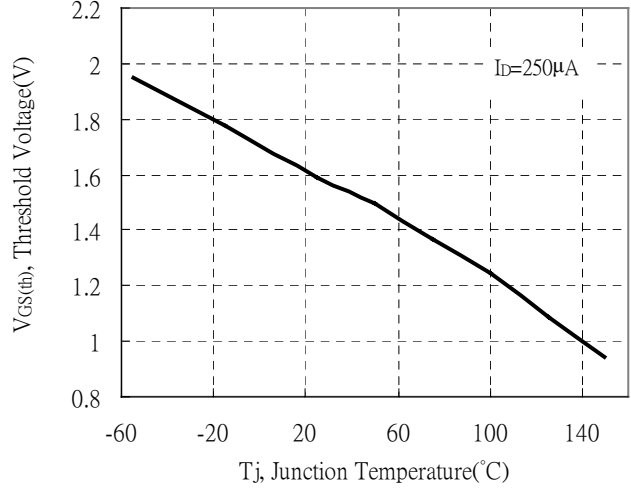


Typical Characteristics(Cont.)

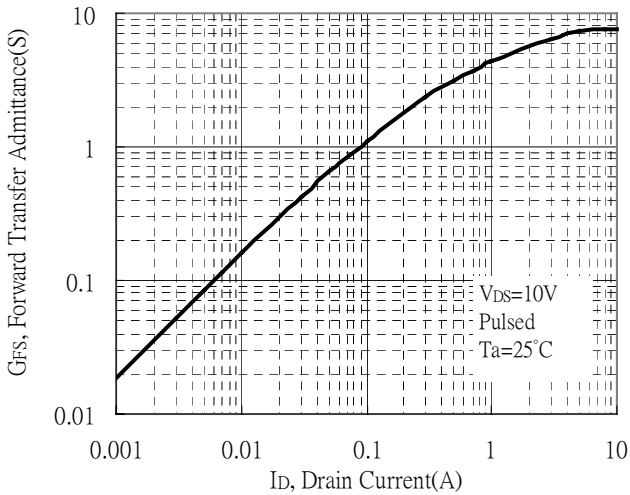
Capacitance vs Drain-to-Source Voltage



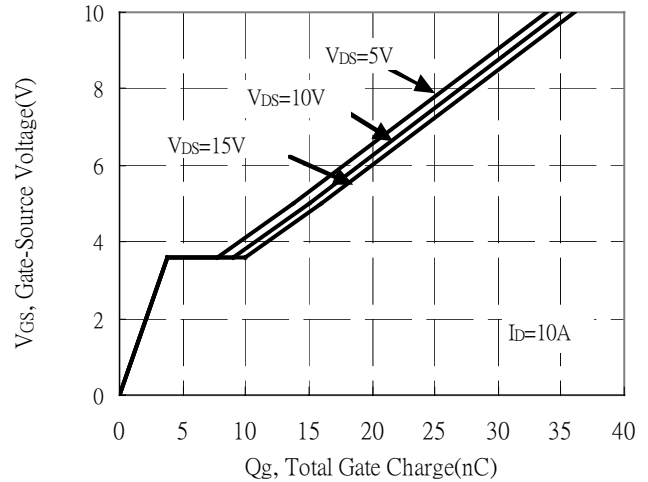
Threshold Voltage vs Junction Temperature



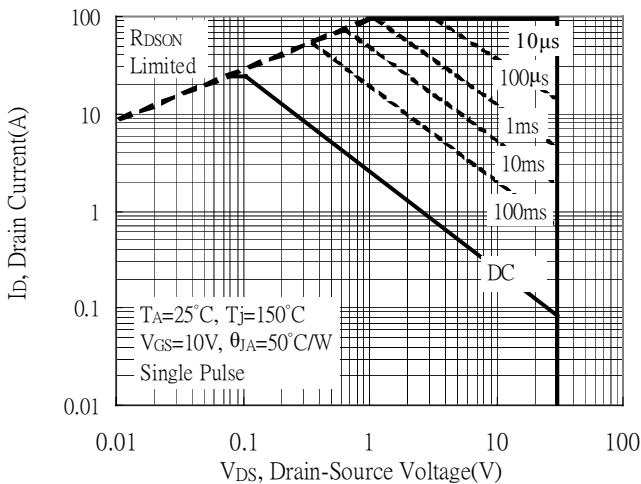
Forward Transfer Admittance vs Drain Current



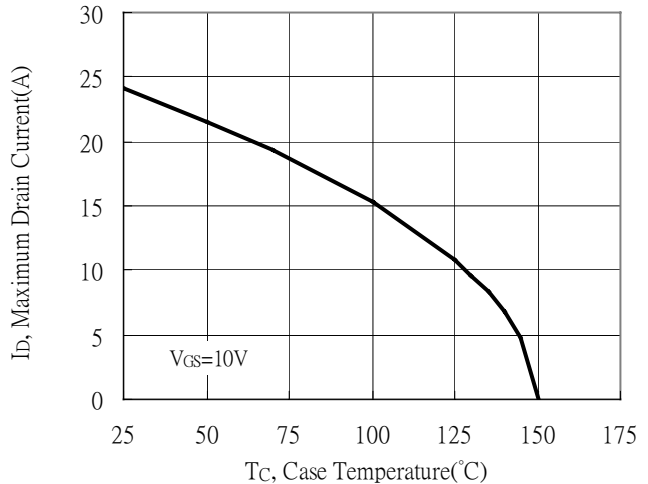
Gate Charge Characteristics



Maximum Safe Operating Area

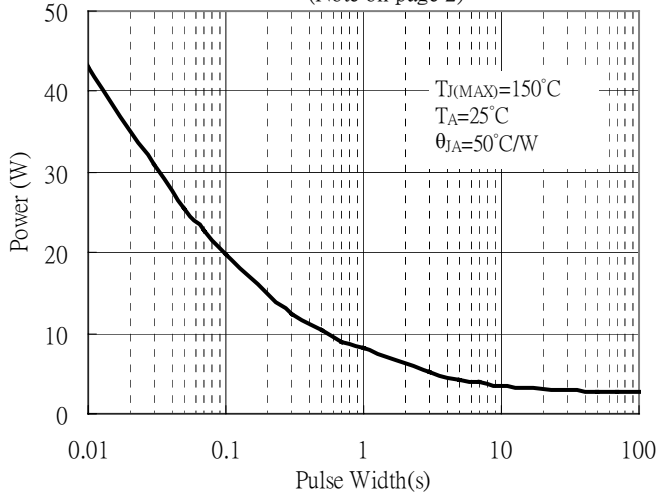


Maximum Drain Current vs Case Temperature

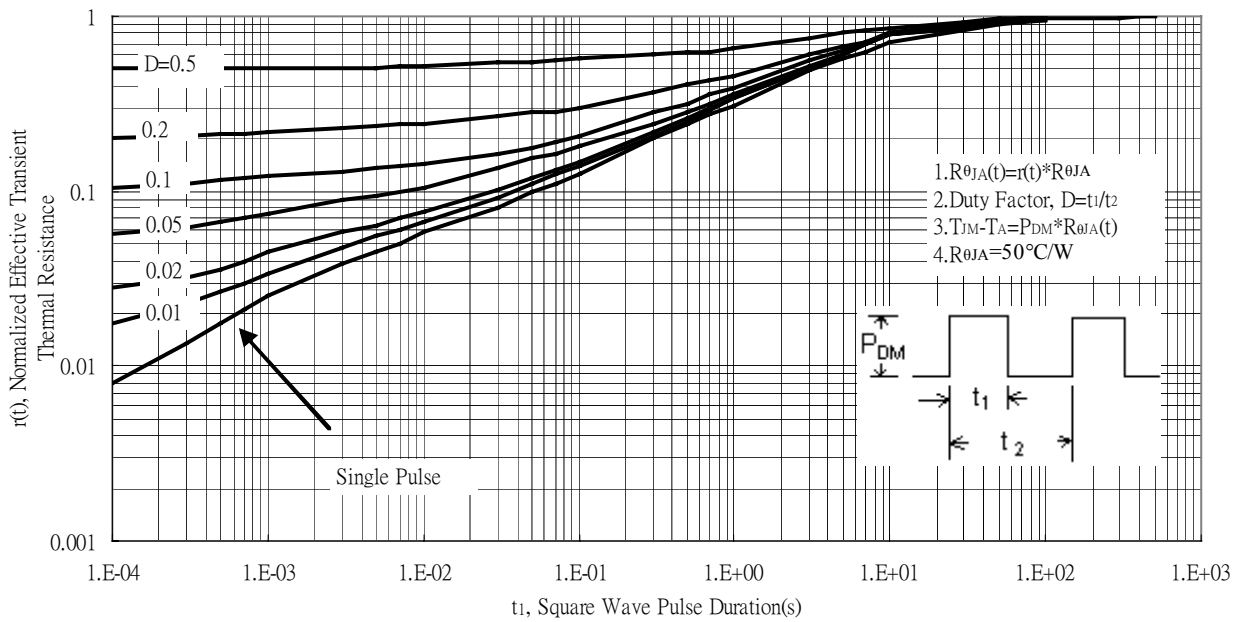


Typical Characteristics(Cont.)

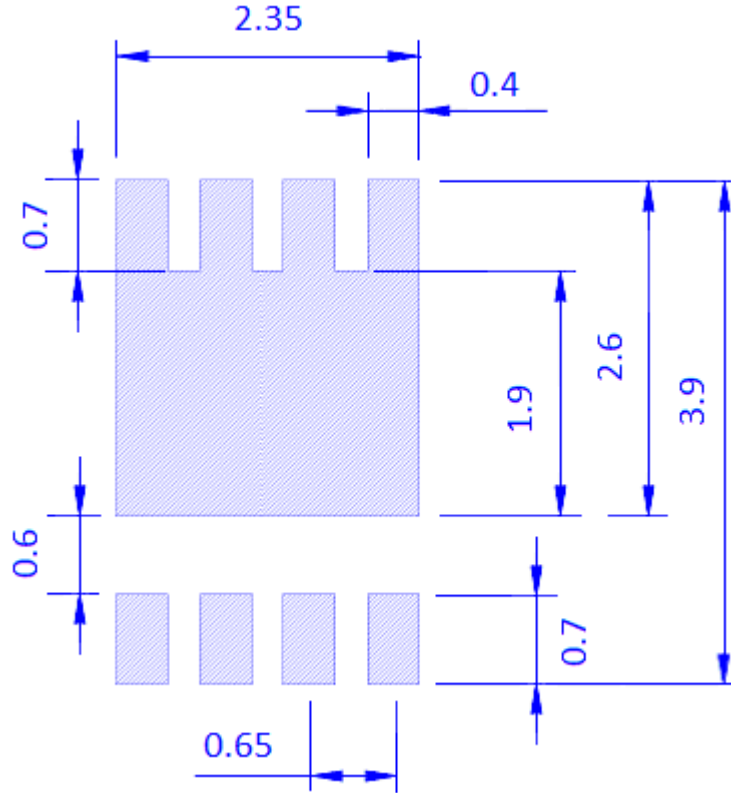
Single Pulse Power Rating, Junction to Ambient
 (Note on page 2)



Transient Thermal Response Curves

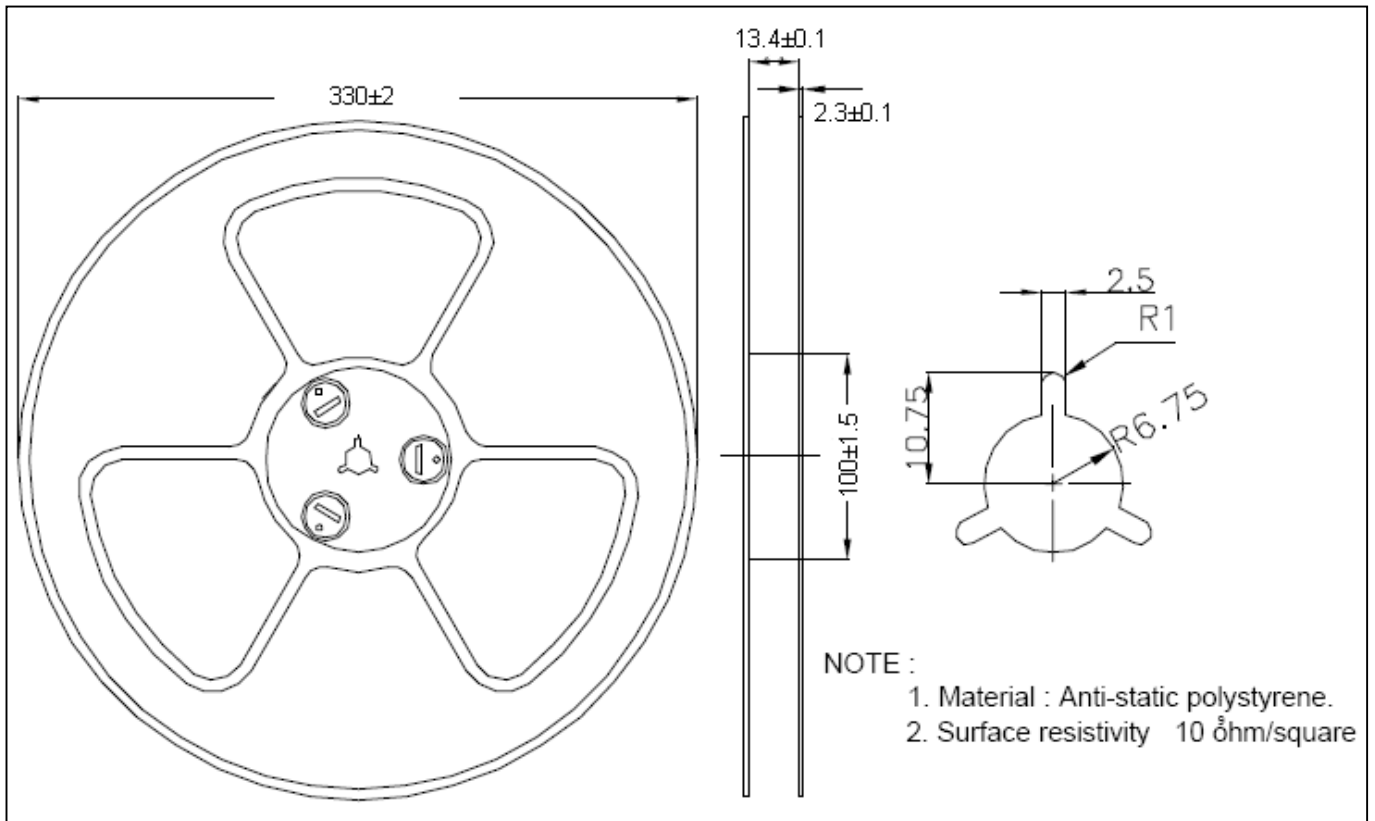


Recommended Soldering Footprint

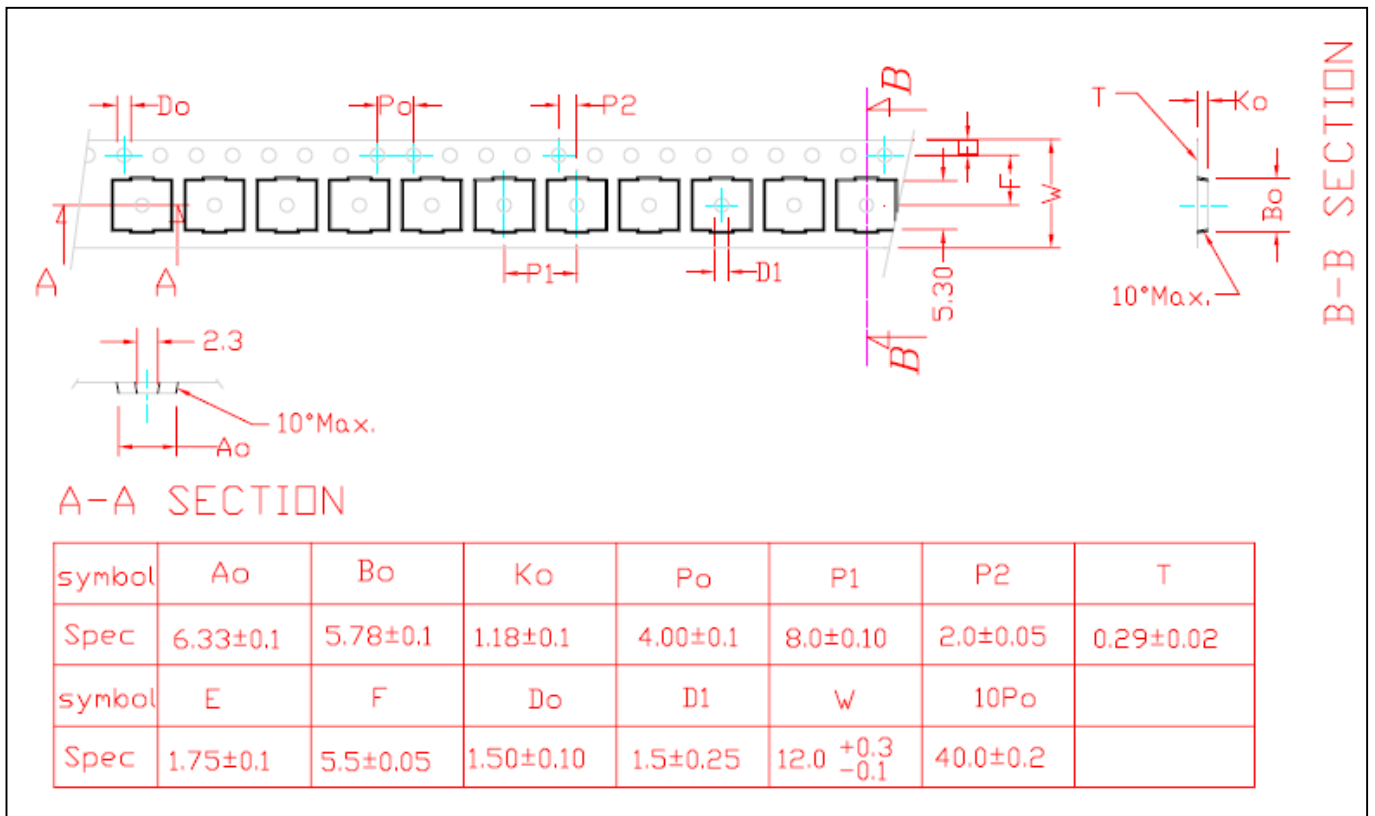


unit : mm

Reel Dimension

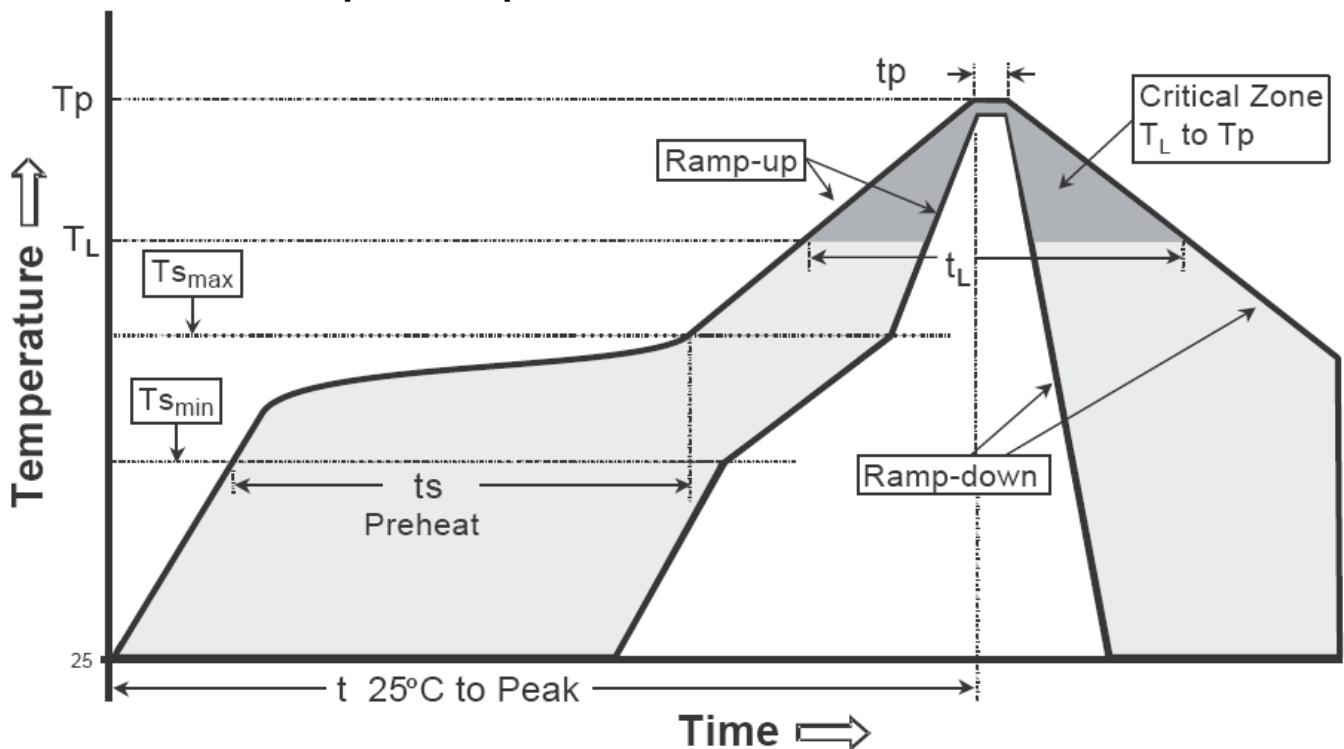


Carrier Tape Dimension



Recommended wave soldering condition

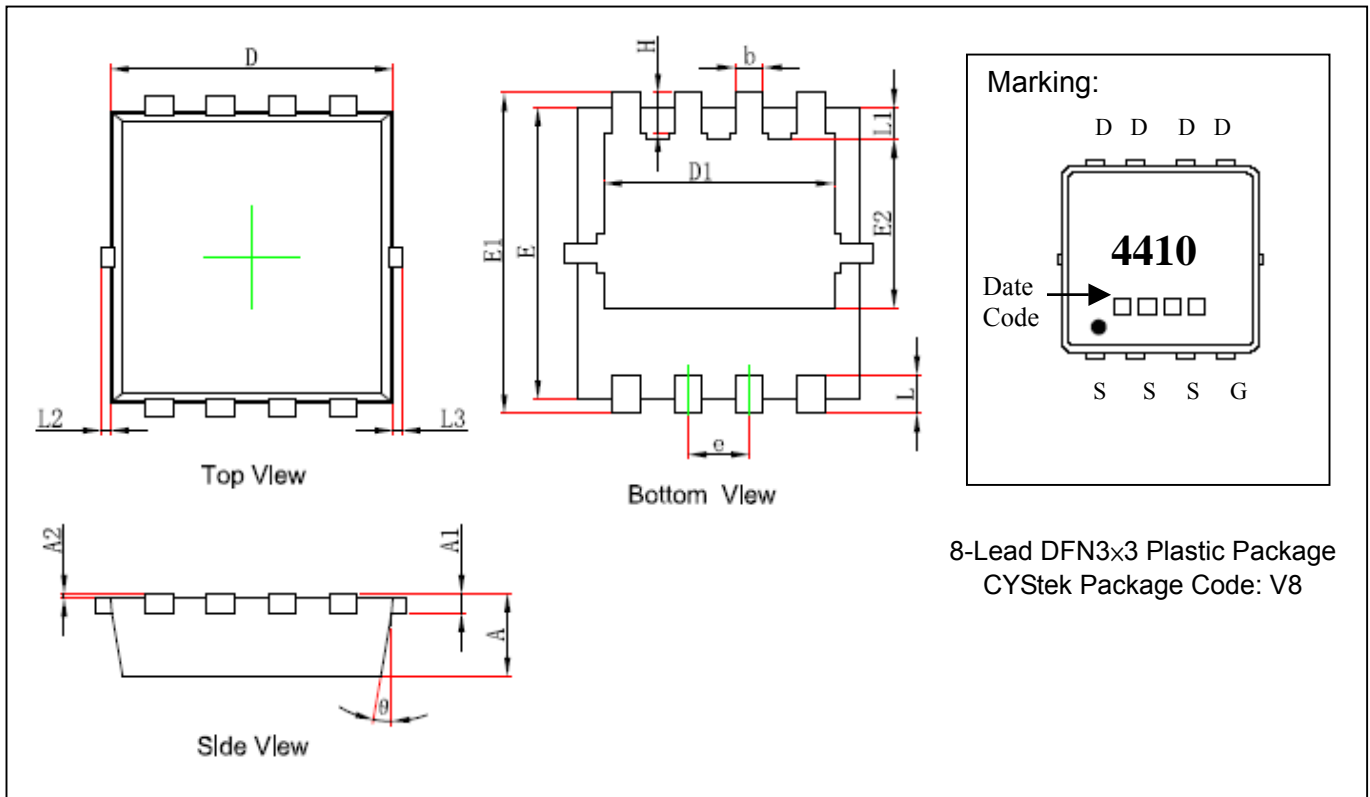
| | | |
|-----------------|------------------|-----------------|
| Product | Peak Temperature | Soldering Time |
| Pb-free devices | 260 +0/-5 °C | 5 +1/-1 seconds |

Recommended temperature profile for IR reflow


| Profile feature | Sn-Pb eutectic Assembly | Pb-free Assembly |
|--|-------------------------|------------------|
| Average ramp-up rate (Tsmax to Tp) | 3°C/second max. | 3°C/second max. |
| Preheat | | |
| -Temperature Min(Ts min) | 100°C | 150°C |
| -Temperature Max(Ts max) | 150°C | 200°C |
| -Time(ts min to ts max) | 60-120 seconds | 60-180 seconds |
| Time maintained above: | | |
| -Temperature (Tl) | 183°C | 217°C |
| - Time (tl) | 60-150 seconds | 60-150 seconds |
| Peak Temperature(Tp) | 240 +0/-5 °C | 260 +0/-5 °C |
| Time within 5°C of actual peak temperature(tp) | 10-30 seconds | 20-40 seconds |
| Ramp down rate | 6°C/second max. | 6°C/second max. |
| Time 25 °C to peak temperature | 6 minutes max. | 8 minutes max. |

Note : All temperatures refer to topside of the package, measured on the package body surface.

DFN3x3 Dimension



*: Typical

| DIM | Millimeters | | Inches | | DIM | Millimeters | | Inches | |
|-----|-------------|-------|--------|-------|-----|-------------|-------|--------|-------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Min. | Max. |
| A | 0.605 | 0.850 | 0.026 | 0.033 | b | 0.200 | 0.400 | 0.008 | 0.016 |
| A1 | 0.152 | REF | 0.006 | REF | e | 0.550 | 0.750 | 0.022 | 0.030 |
| A2 | 0.000 | 0.050 | 0.000 | 0.002 | L | 0.300 | 0.500 | 0.012 | 0.020 |
| D | 2.900 | 3.100 | 0.114 | 0.122 | L1 | 0.180 | 0.480 | 0.007 | 0.019 |
| D1 | 2.300 | 2.600 | 0.091 | 0.102 | L2 | 0.000 | 0.100 | 0.000 | 0.004 |
| E | 2.900 | 3.100 | 0.114 | 0.122 | L3 | 0.000 | 0.100 | 0.000 | 0.004 |
| E1 | 3.150 | 3.450 | 0.124 | 0.136 | H | 0.315 | 0.515 | 0.012 | 0.020 |
| E2 | 1.535 | 1.935 | 0.060 | 0.076 | θ | 9° | 13° | 9° | 13° |

Notes: 1. Controlling dimension: millimeters.
 2. Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3. If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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